sapcon®

13003

NPN高压开关晶体管/NPN High Switching Transistor

●特点：■击穿的电压稳定■开关速度快■安全工作区宽■符合ROHS规范

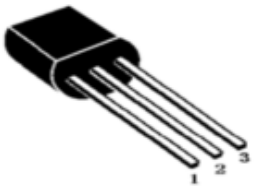
●FEATURES:■HIGH VOLTAGE CAPABILITY ■HIGH SPEED SWITCHING ■WIDE SOA ■ROHS COMPLIANT

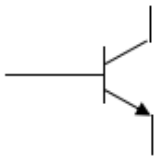
●应用■节能灯■电子镇流器■电子变压器等开关电路

●APPLICATION:■FLUORESCENT LAMP ■ELECTRONIC BALLAST ■ELECTRONIC TRANSFORMER ECT.

● 最大额定值（TC=25℃） Absoolute Maximum Rantings (Tc=25℃)

参数名称 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
集电极-基极电压 Collector-Base Voltage	VCBO	600	V
集电极-发射极电压 Collector-Emitter Voltage	VCEO	400	V
发射极-基极 Emitter-Base Voltage	VEBO	9	V
集电极电流 Collector Current	IC	1.2	A
集电极耗散功率 Total Power Dissipation	PC	16	W
最高工作温度 Junction Temperature	Tj	150	℃
贮存温度 Storage Temperature	TsTg	-65-150	℃





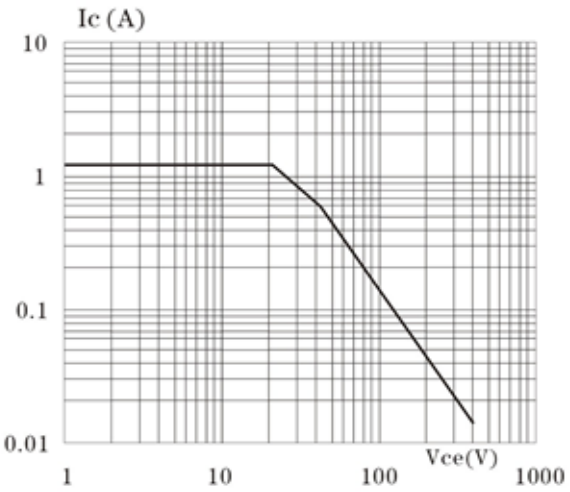
封装形式：TO-92

● 电特性（TC=25℃）Electronic Characteristics(Tc=25℃)

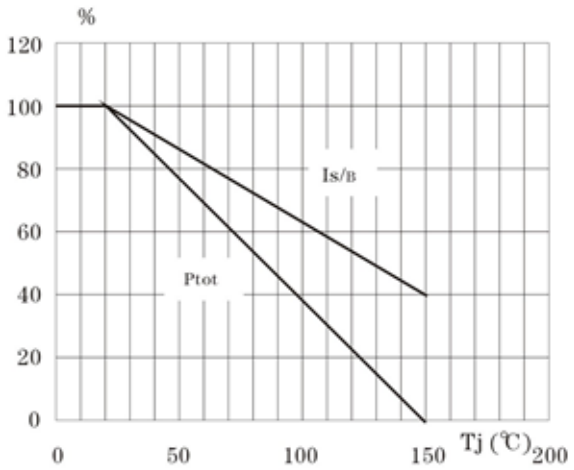
参数名称 CHARACTERISTICS	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	最大值 MAX	单位 UNIT
集电极-基极截止电流 Collector-Base Cutoff Current	ICBO	VCB=600V		5	uA
集电极-发射极截止电流 Collector-Emitter Cutoff Current	ICEO	VCE=400V, IB=0		10	uA
集电极-发射极电压 Collector-Emitter Voltage	VCEO	IC=10mA, IB=0	410		V
发射极-基极电压 Collector-Base Voltage	VEBO	IE=1mA, IC=0	9		V
集电极-发射极饱和压降 Collector-Emitter Saturation Voltage	Vcesat	IC=200mA, IB=40mA		0.3	
		IC=500mA, IB=10mA		0.45	V
		IC=1.0A, IB=0.25A		0.65	V
发射极-基极饱和压降Base-Emitter Saturation Voltage	Vbesat	IC=1.0A, IB=0.25A		1.2	V
电流放大倍数 DC Current Gain	Hfe	VCE=5V, IC=200uA	8		
		VCE=5V, IC=200mA	15	30	
		VCE=5V, IC=1A	6		
贮存时间 Storage Time	ts	VCC=5V IC=0.25A (UI9600)	4.0	8.0	us
下降时间 falling time	tf			1.0	

特性曲线 ELECTRICAL CHARACTERISTICS(curves)

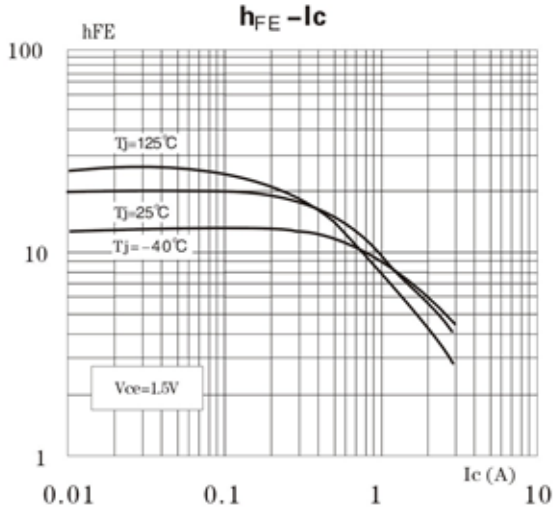
SOA(DC)



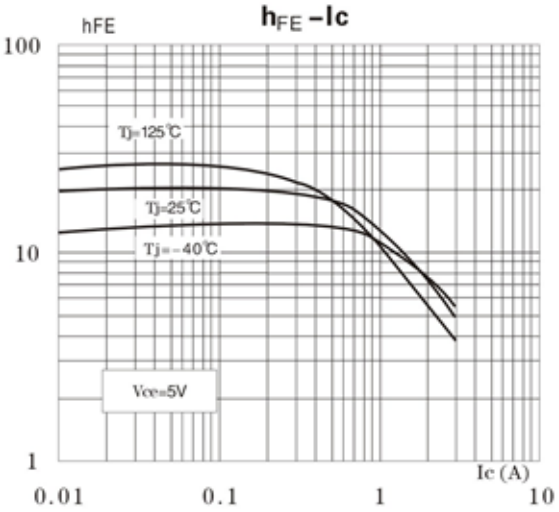
Pc∝Tj



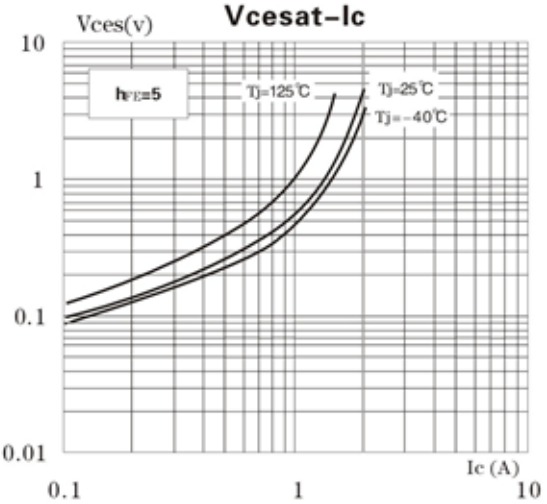
h_{FE} -Ic



h_{FE} -Ic



Vcesat-Ic



Vbesat-Ic